

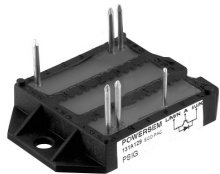
### IGBT Module

Short Circuit SOA Capability  
Square RBSOA

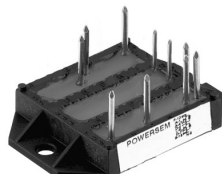
Preliminary Data Sheet

**PSIG 25/06**  
**PSI 25/06\***  
**PSIS 25/06\***  
**PSSI 25/06\***

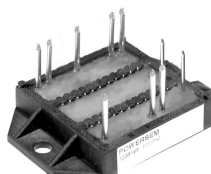
$I_{C25} = 24.5 \text{ A}$   
 $V_{CES} = 600 \text{ V}$   
 $V_{CE(sat)typ.} = 2.4 \text{ V}$



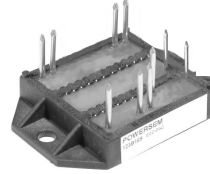
**PSIG 25/06**



**PSI 25/06\***



**PSSI 25/06\***



**PSIS 25/06\***

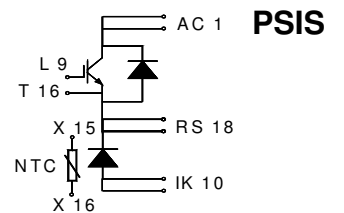
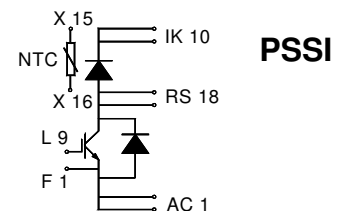
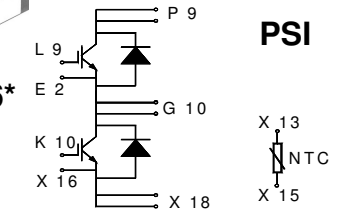
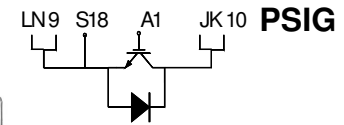
\*NTC optional

### IGBTs

Symbol	Conditions	Maximum Ratings	
$V_{CES}$	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{GES}$		$\pm 20$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	24.5	A
$I_{C80}$	$T_C = 80^\circ\text{C}$	17	A
$I_{CM}$ $V_{CEK}$	$V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega; T_{VJ} = 125^\circ\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	30	A
$t_{SC}$ (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 68 \Omega; T_{VJ} = 125^\circ\text{C}$ non-repetitive	10	$\mu\text{s}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	82	W

Symbol	Conditions	Characteristic Values		
		(T <sub>VJ</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 25 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		2.4	2.9
$V_{GE(th)}$	$I_C = 0.4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$			0.6 2.7
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			100
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 15 \text{ A}$ $V_{GE} = 15/0 \text{ V}; R_G = 68 \Omega$		30	ns
			45	ns
			270	ns
			40	ns
			0.7	mJ
			0.5	mJ
$C_{ies}$	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		8	nF
$R_{thJC}$ $R_{thJH}$	(per IGBT) with heatsink compound (0.42 K/m.K; 50 $\mu\text{m}$ )		3	1.52 K/W

**Caution:** These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.



### Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered, E 148688

### Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

### Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight
- Leads with expansion bend for stress relief

### Reverse diodes (FRED)

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	18.5	A
$I_{F80}$	$T_C = 80^\circ\text{C}$	12.0	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 15\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.58	2.64	V
$I_{RM}$	$I_F = 10\text{ A}; di_F/dt = 400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	7		A
$t_{rr}$		70		ns
$R_{thJC}$	with heatsink compound (0.42 K/m.K; 50 $\mu\text{m}$ )		3.5	K/W
$R_{thJH}$		7		K/W

### Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$	$T = 25^\circ\text{C}$	4.75	5.0	k $\Omega$
$B_{25/50}$			3375	K

### Module

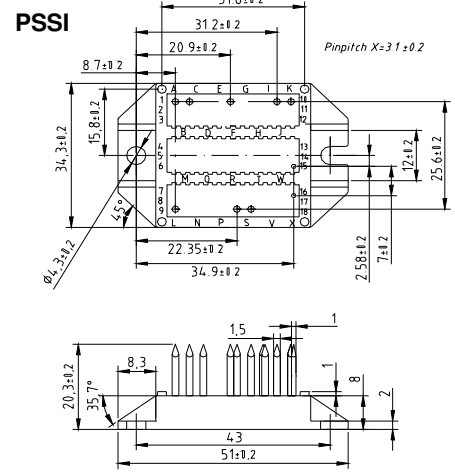
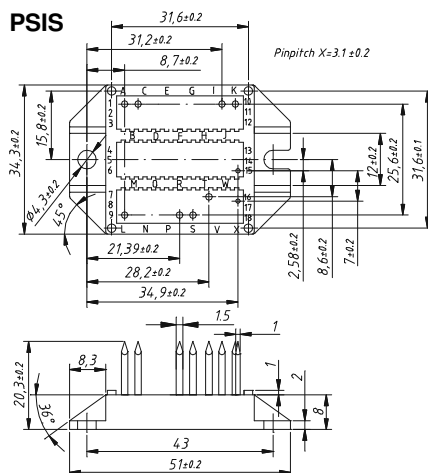
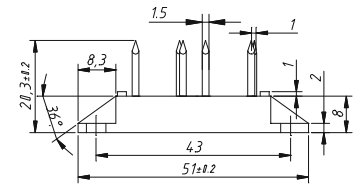
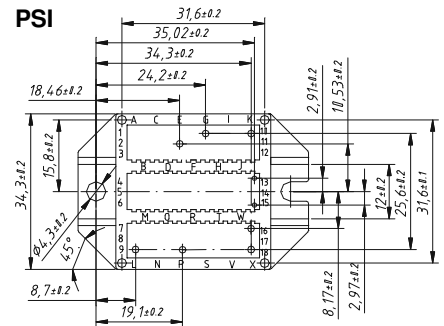
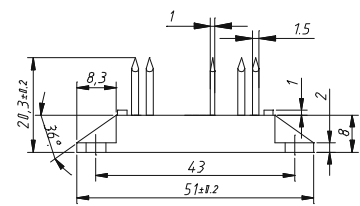
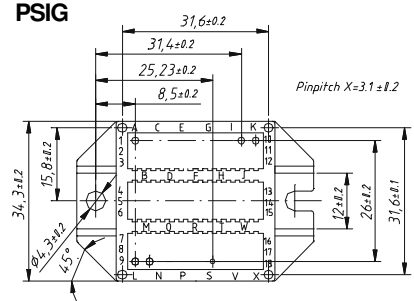
Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{stg}$		-40...+150	$^\circ\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	3000	V~
$M_d$	Mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
$a$	Max. allowable acceleration	50	$\text{m/s}^2$

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$d_S$	Creepage distance on surface (Pin to heatsink)	11.2		mm
$d_A$	Strike distance in air (Pin to heatsink)	11.2		mm

<b>Weight</b>		24	g
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### Package style and outline

Dimensions in mm (1mm = 0.0394")



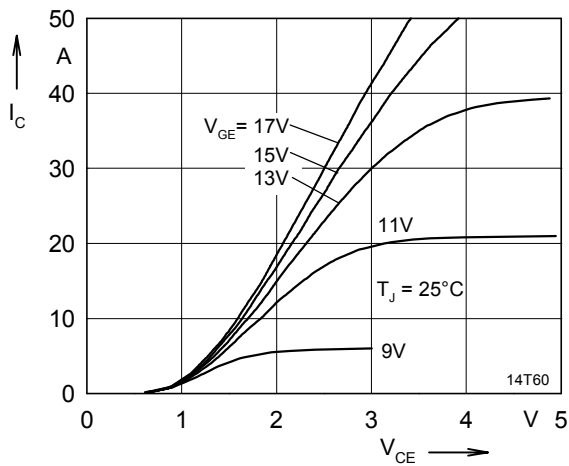


Fig. 1 Typ. output characteristics

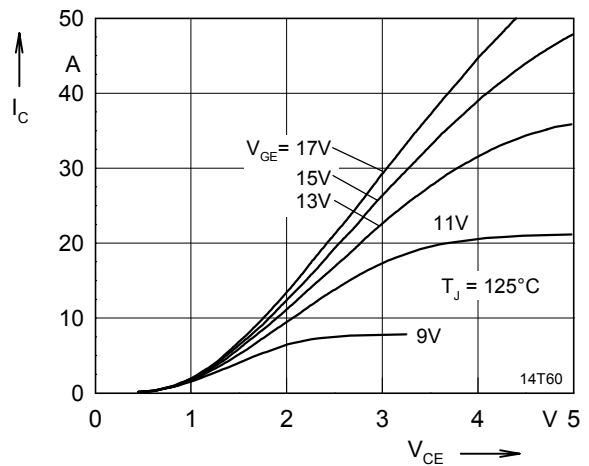


Fig. 2 Typ. output characteristics

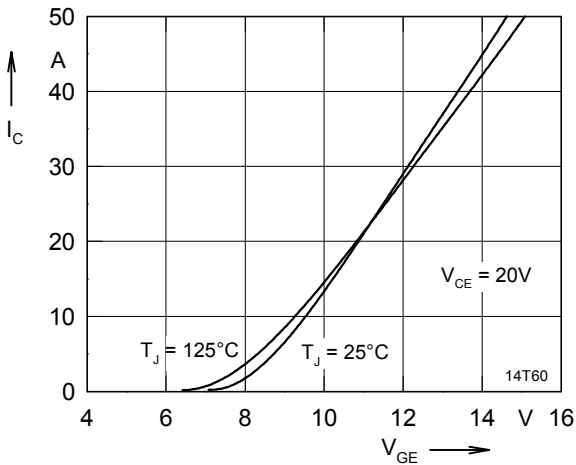


Fig. 3 Typ. transfer characteristics

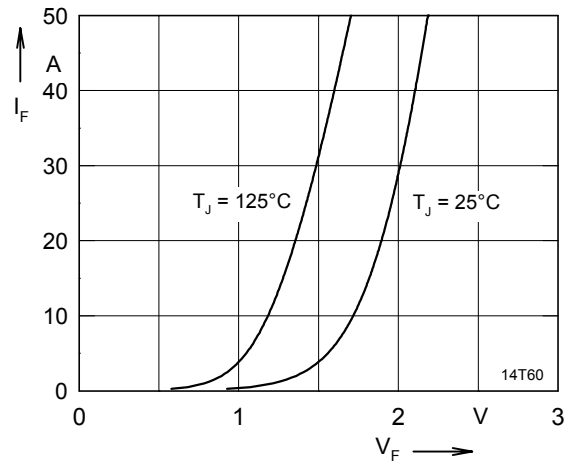


Fig. 4 Typ. forward characteristics of free wheeling diode

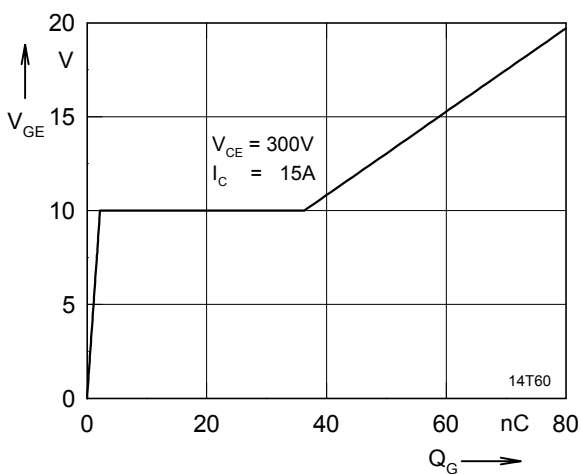


Fig. 5 Typ. turn on gate charge

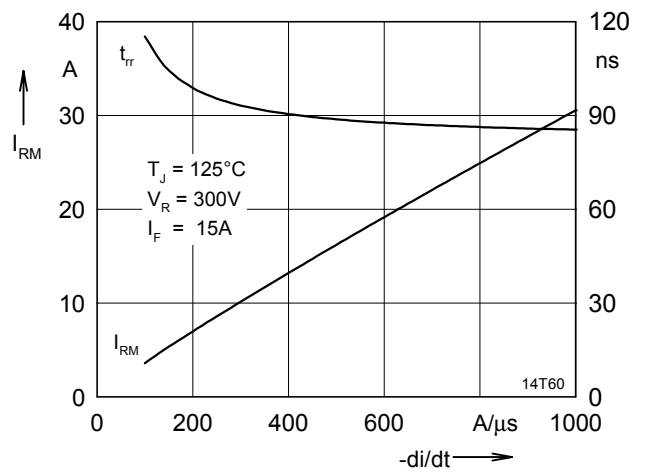


Fig. 6 Typ. turn off characteristics of free wheeling diode

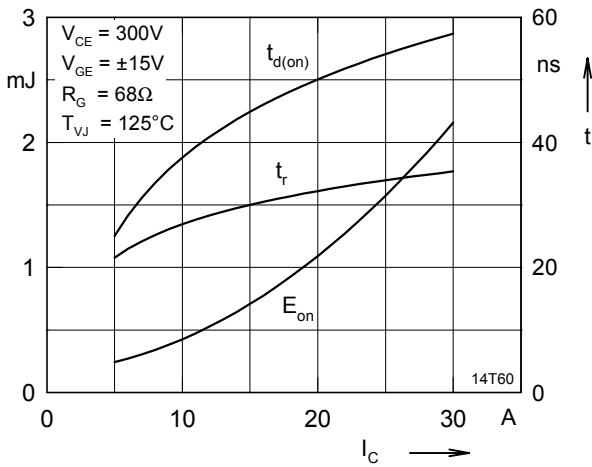


Fig. 7 Typ. turn on energy and switching

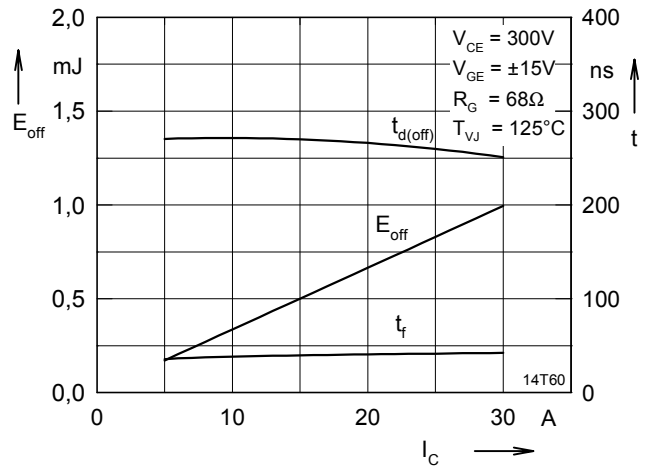


Fig. 8 Typ. turn off energy and switching times versus collector current times versus collector current

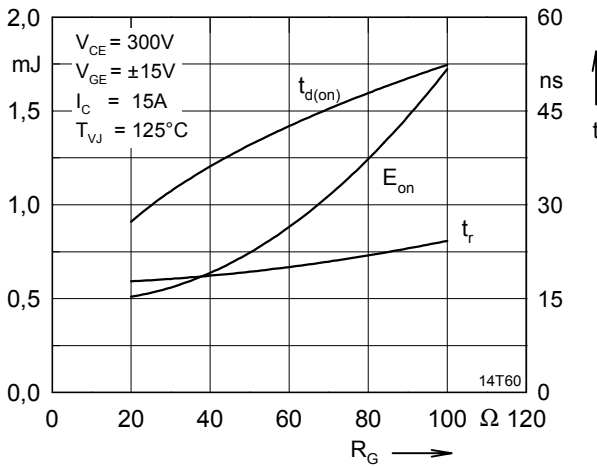


Fig. 9 Typ. turn on energy and switching

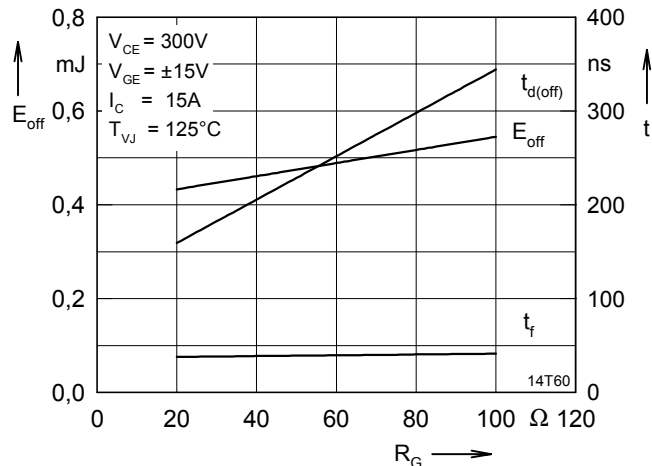


Fig. 10 Typ. turn off energy and switching times versus gate resistor times versus gate resistor

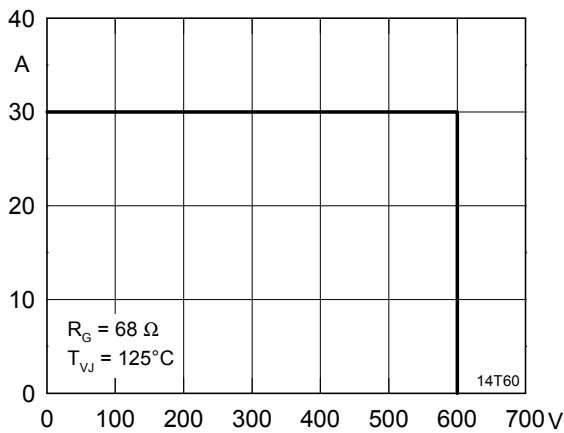


Fig. 11 Reverse biased safe operating area

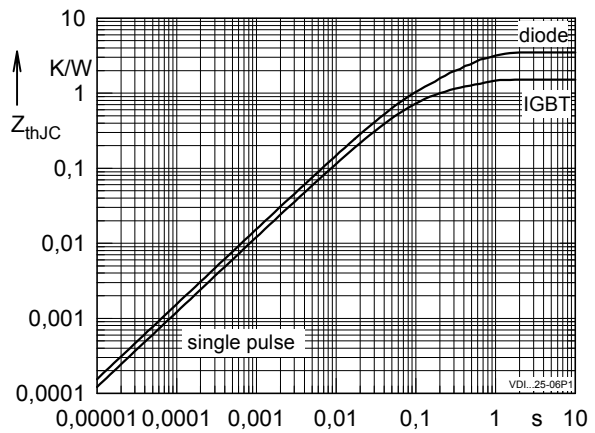


Fig. 12 Typ. transient thermal impedance RBSOA